NSN 5961-01-051-6655



Transistor - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-01-051-6655 **Inclosure Material:** Ceramic **Overall Length:** Between 0.890 inches and 0.910 inches **Overall Height:** 0.240 inches **Overall Width:** Between 0.376 inches and 0.410 inches **End Application:** An/fps-115 **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 65.0 collector to base voltage/static/emitter open and 25.0 collector to emitter voltage/static/base open and 4.0 emitter to base voltage, instantaneous **Current Rating Per Characteristic:** 5.00 amperes source cutoff current **Power Rating Per Characteristic:** 40.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** The ceramic body of this device contains beryllium oxide. Do not crush, grind or abrade these portions because the dust resulting from such action may be hazardous if inhaled, disposal should be in accordance with federal and state regulations; t.O 31p6-2fps115-62; n/h/a radar transmitter; junction pattern arrangement: npn **Terminal Type And Quantity:** 2 ribbon and 1 tab, solder lug Shelf Life: N/a **Unit Of Measure:**

Demilitarization:

No

Fiig:

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